



1. Description

SS014N04MS, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for DC-DC and high speed switching applications.

KEY CHARACTERISTICS

Parameter	Value	Unit
V_{DS}	40	V
I_D	180	A
$R_{DS(on).typ}$	1.2	mΩ

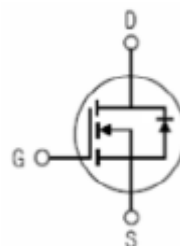
FEATURES

- Fast Switching
- Low On-Resistance ($R_{DS(on)} \leq 1.4m\Omega$)
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

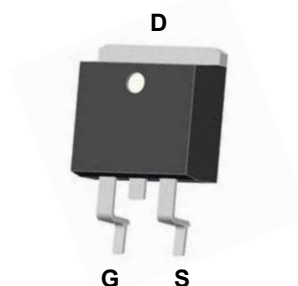
APPLICATIONS

- Switching applications
- DC-DC Converters
- BMS

Inner Equivalent Principium Chart



TO-263-2L top view



ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing
SS014N04MS	TO-263	SS014N04MS	Reel